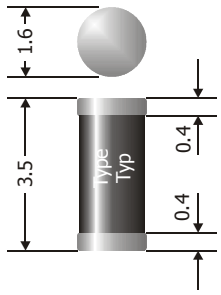
Diotec Semiconductor

BR100-03LLD ... BR100-04LLD

Surface Mount Bidirectional Si-Trigger-Diodes (DIAC)
Bidirektionale Si-Triggerdioden für die Oberflächenmontage (DIAC)

Version 2006-04-27



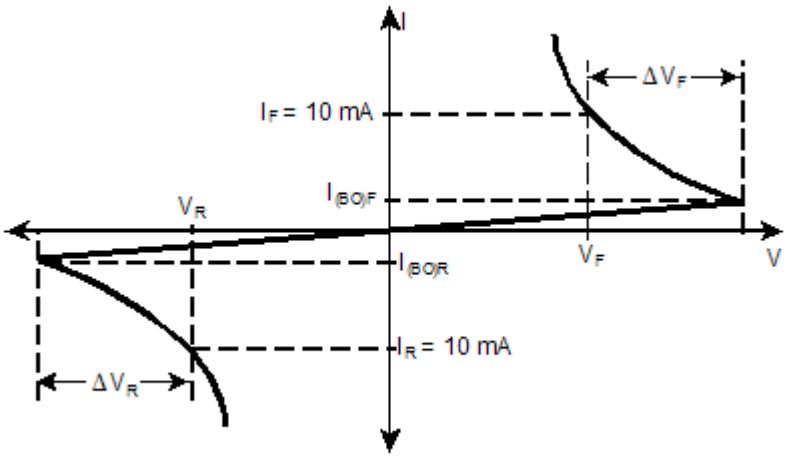
Dimensions - Maße [mm]

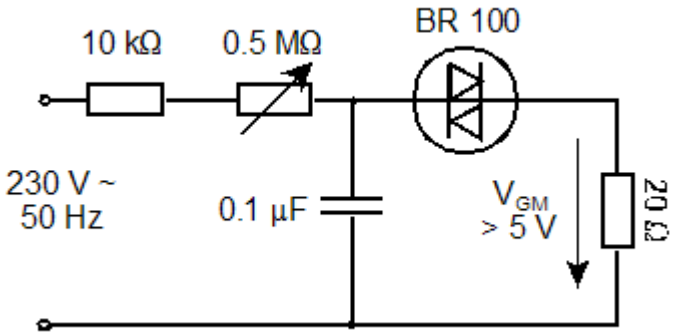
Breakover voltage Durchbruchspannung	28 ... 45 V
Plastic case MiniMELF Kunststoffgehäuse MiniMELF	DO-213AA
Weight approx. – Gewicht ca.	0.04 g
Plastic material has UL classification 94V-0 Gehäusematerial UL94V-0 klassifiziert	
Standard packaging taped and reeled Standard Lieferform gegurtet auf Rolle	

Maximum ratings			**Grenzwerte**
Power dissipation Verlustleistung	T_A = 50°C	P_{tot}	150 mW [1])
Peak pulse current (120 Hz pulse repetition rate) Max. Triggerstrom (120 Hz Puls-Wiederholrate)	$t_p \leq 20$ µs	I_{PM}	± 2 A [1])
Operating Junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur		T_j T_S	-50...+100°C -50...+175°C

Characteristics				**Kennwerte**
Breakover voltage Durchbruchspannung	dV/dt = 10 V/µs	BR100-03LLD BR100-031LLD BR100-04LLD	V_{BO} V_{BO} V_{BO}	28 ... 36 V 30 ... 34 V 35 ... 45 V
Breakover current – Durchbruchstrom		V = 98% V_{BO}	I_{BO}	< 50 µA
Asymmetry of breakover voltage Unsymmetrie der Durchbruchspannung		$\lvert V_{(BO)F} - V_{(BO)R} \rvert$	ΔV_{BO}	< 3.8 V
Foldback voltage – Spannungs-Rücksprung $\Delta I = I_{BO}$ to/auf I_F = 10 mA		dV/dt = 10 V/µs	$\Delta V_{F/R}$	> 5 V
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft			R_{thA}	< 150 K/W [1])
Thermal resistance junction to terminal Wärmewiderstand Sperrschicht – Anschluss			R_{thT}	< 70 K/W

1 Mounted on P.C. board with 25 mm² copper pads at each terminal
Montage auf Leiterplatte mit 25 mm² Kupferbelag (Lötpad) an jedem Anschluss





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